

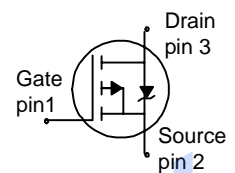
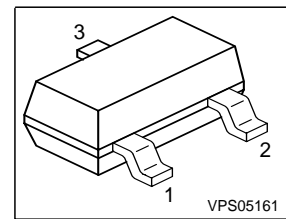
**SIPMOS<sup>®</sup> Small-Signal-Transistor**
**Feature**

- P-Channel
- Enhancement mode
- Logic Level
- Avalanche rated
- $dv/dt$  rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$	-60	V
$R_{DS(on)}$	8	$\Omega$
$I_D$	-0.17	A

PG-SOT-23



Type	Package	Tape and Reel	Marking
BSS84P	PG-SOT-23	H6327:3000pcs/r.	YBs
BSS84P	PG-SOT-23	H6433:10000pcs/r.	YBs

**Maximum Ratings, at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Value	Unit
Continuous drain current	$I_D$		A
$T_A=25\text{ }^\circ\text{C}$		-0.17	
$T_A=70\text{ }^\circ\text{C}$		-0.14	
Pulsed drain current	$I_{D\text{ puls}}$	-0.68	
$T_A=25\text{ }^\circ\text{C}$			
Avalanche energy, single pulse	$E_{AS}$	2.6	mJ
$I_D=-0.17\text{ A}$ , $V_{DD}=-25\text{ V}$ , $R_{GS}=25\text{ }\Omega$			
Avalanche energy, periodic limited by $T_{jmax}$	$E_{AR}$	0.036	
Reverse diode $dv/dt$	$dv/dt$	-6	kV/ $\mu\text{s}$
$I_S=-0.17\text{ A}$ , $V_{DS}=-48\text{ V}$ , $di/dt=-200\text{ A}/\mu\text{s}$ , $T_{jmax}=150\text{ }^\circ\text{C}$			
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation	$P_{tot}$	0.36	W
$T_A=25\text{ }^\circ\text{C}$			
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class JEESD22-A114-HBM		Class 0	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - soldering point (Pin 3)	$R_{thJS}$	-	-	200	K/W
SMD version, device on PCB: @ min. footprint	$R_{thJA}$	-	-	350	
@ 6 cm <sup>2</sup> cooling area <sup>1)</sup>		-	-	300	

**Electrical Characteristics, at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain-source breakdown voltage $V_{GS}=0, I_D=-250\mu\text{A}$	$V_{(BR)DSS}$	-60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-20\mu\text{A}$	$V_{GS(th)}$	-1	-1.5	-2	
Zero gate voltage drain current $V_{DS}=-60\text{V}, V_{GS}=0, T_A=25^\circ\text{C}$ $V_{DS}=-60\text{V}, V_{GS}=0, T_A=125^\circ\text{C}$	$I_{DSS}$	-	-0.1	-1	$\mu\text{A}$
Gate-source leakage current $V_{GS}=-20\text{V}, V_{DS}=0$	$I_{GSS}$	-	-10	-100	
Drain-source on-state resistance $V_{GS}=-4.5\text{V}, I_D=-0.14\text{A}$	$R_{DS(on)}$	-	8	12	$\Omega$
Drain-source on-state resistance $V_{GS}=-10\text{V}, I_D=-0.17\text{A}$	$R_{DS(on)}$	-	5.8	8	

<sup>1)</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics, at  $T_A = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic Characteristics**

Transconductance	$g_{fs}$	$V_{DS} \leq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = -0.14A$	0.065	0.13	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0, V_{DS} = -25V,$ $f = 1MHz$	-	15	19	pF
Output capacitance	$C_{oss}$		-	6	8	
Reverse transfer capacitance	$C_{rss}$		-	2	3	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -30V, V_{GS} = -4.5V,$ $I_D = -0.14A, R_G = 25\Omega$	-	6.7	10	ns
Rise time	$t_r$		-	16.2	24.3	
Turn-off delay time	$t_{d(off)}$		-	8.6	12.9	
Fall time	$t_f$		-	20.5	30.8	

**Gate Charge Characteristics**

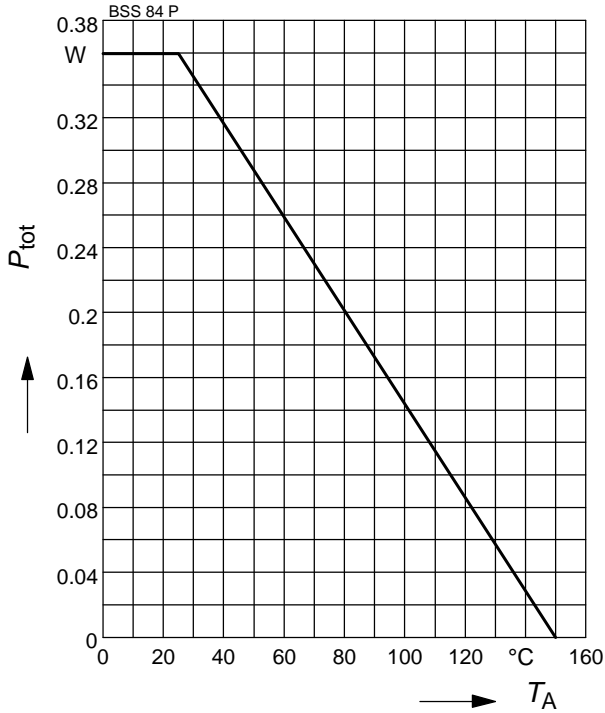
Gate to source charge	$Q_{gs}$	$V_{DD} = -48V, I_D = -0.17A$	-	0.25	0.37	nC
Gate to drain charge	$Q_{gd}$		-	0.3	0.45	
Gate charge total	$Q_g$	$V_{DD} = -48V, I_D = -0.17A,$ $V_{GS} = 0 \text{ to } -10V$	-	1	1.5	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = -48V, I_D = -0.17A$	-	-3.42	-	V

**Reverse Diode**

Inverse diode continuous forward current	$I_S$	$T_A = 25\text{ °C}$	-	-	-0.17	A
Inv. diode direct current, pulsed	$I_{SM}$		-	-	-0.68	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0, I_F = -0.17A$	-	-0.93	-1.24	V
Reverse recovery time	$t_{rr}$	$V_R = -30V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	-	23	34	ns
Reverse recovery charge	$Q_{rr}$		-	10	15	nC

**1 Power dissipation**

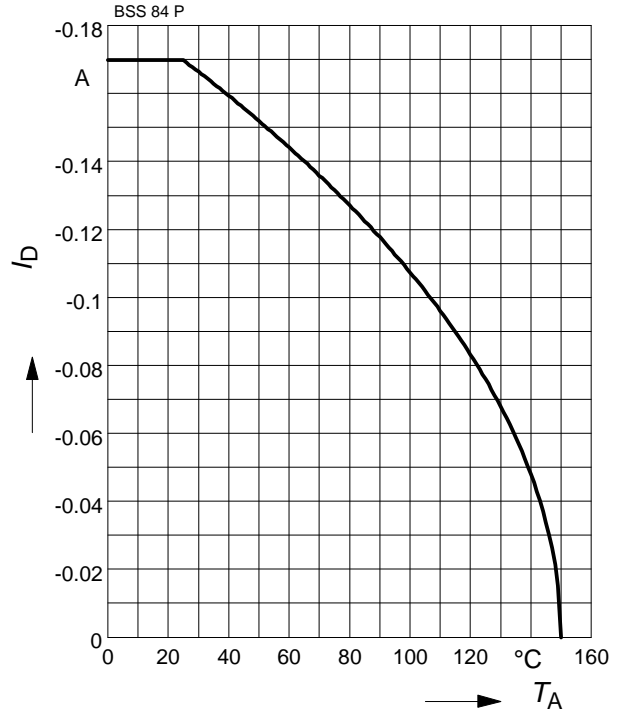
$P_{tot} = f(T_A)$



**2 Drain current**

$I_D = f(T_A)$

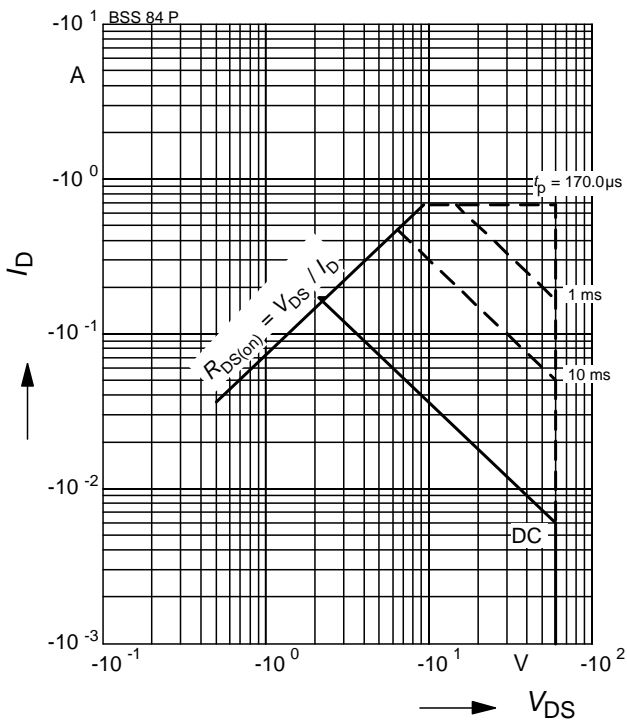
parameter:  $V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D = f(V_{DS})$

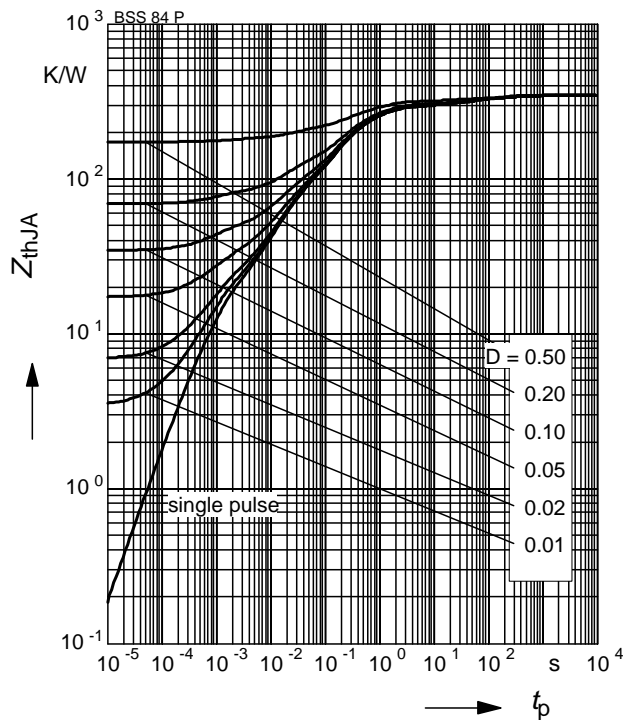
parameter:  $D = 0$ ,  $T_A = 25\text{ °C}$



**4 Transient thermal impedance**

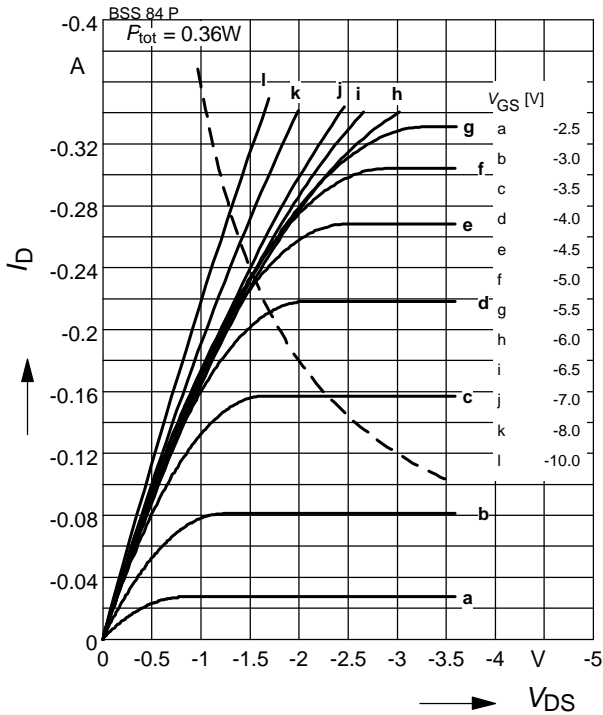
$Z_{thJA} = f(t_p)$

parameter:  $D = t_p/T$

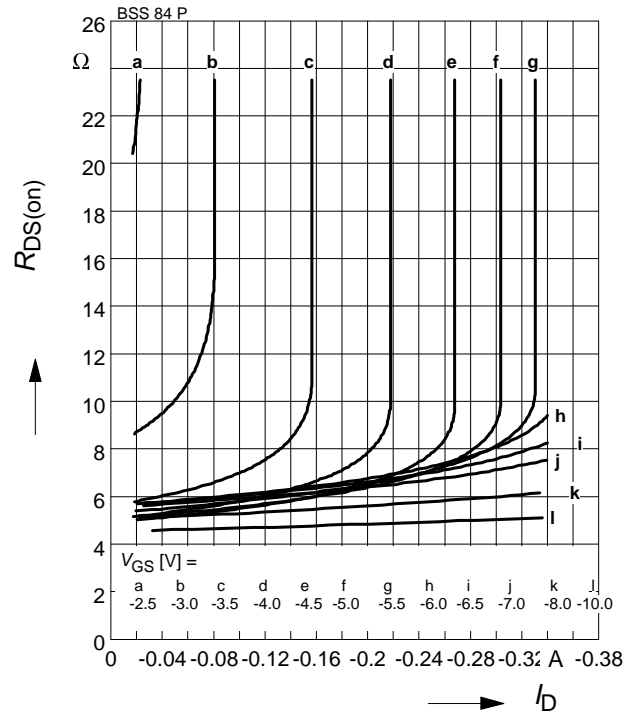


**5 Typ. output characteristic**

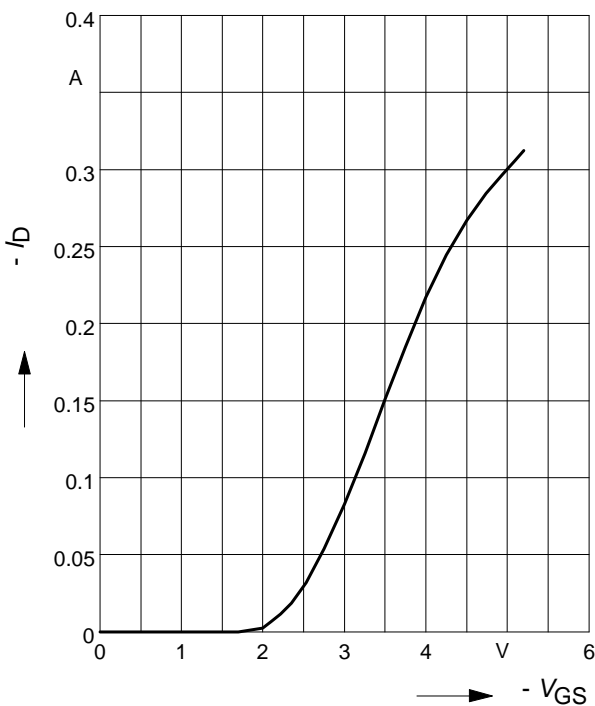
$$I_D = f(V_{DS})$$

 parameter:  $T_j = 25\text{ }^\circ\text{C}$ 

**6 Typ. drain-source on resistance**

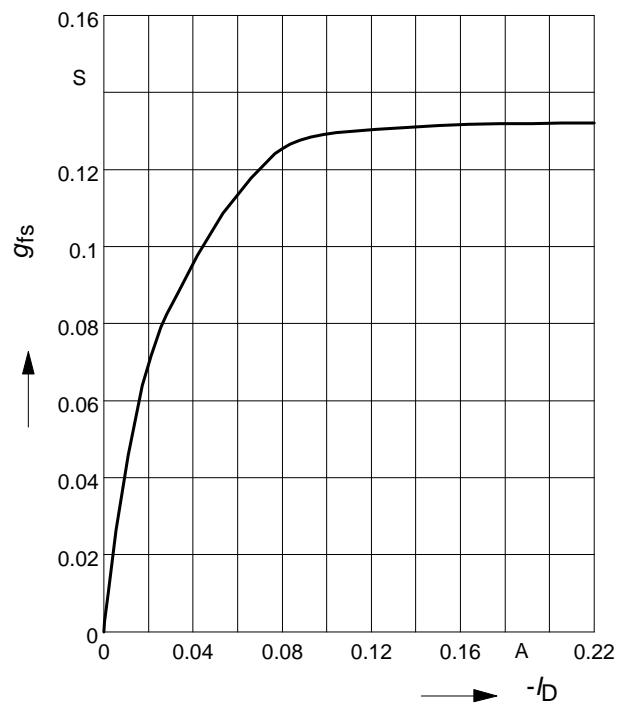
$$R_{DS(on)} = f(I_D)$$

 parameter:  $V_{GS}$ ;  $T_j = 25\text{ }^\circ\text{C}$ 

**7 Typ. transfer characteristics**

$$I_D = f(V_{GS}); |V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$$

 parameter:  $T_j = 25\text{ }^\circ\text{C}$ 

**8 Typ. forward transconductance**

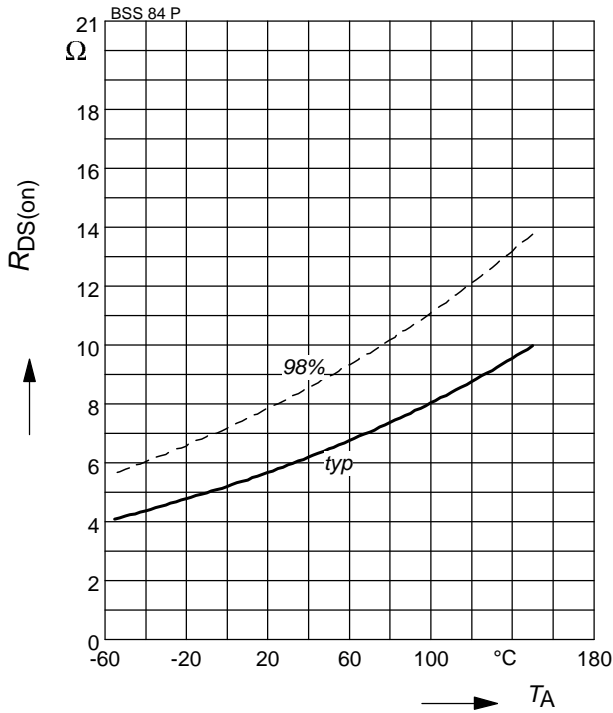
$$g_{fs} = f(I_D)$$

 parameter:  $T_j = 25\text{ }^\circ\text{C}$ 


**9 Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

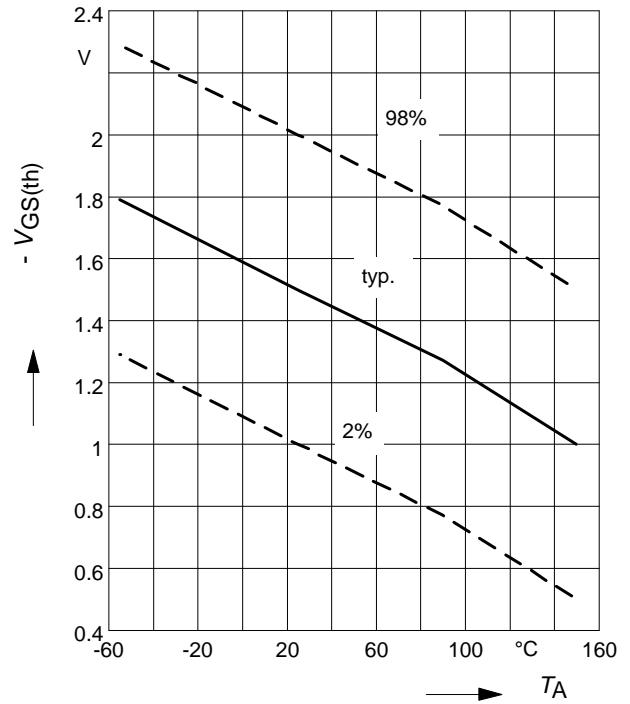
parameter :  $I_D = -0.17 \text{ A}$ ,  $V_{GS} = -10 \text{ V}$



**10 Typ. gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

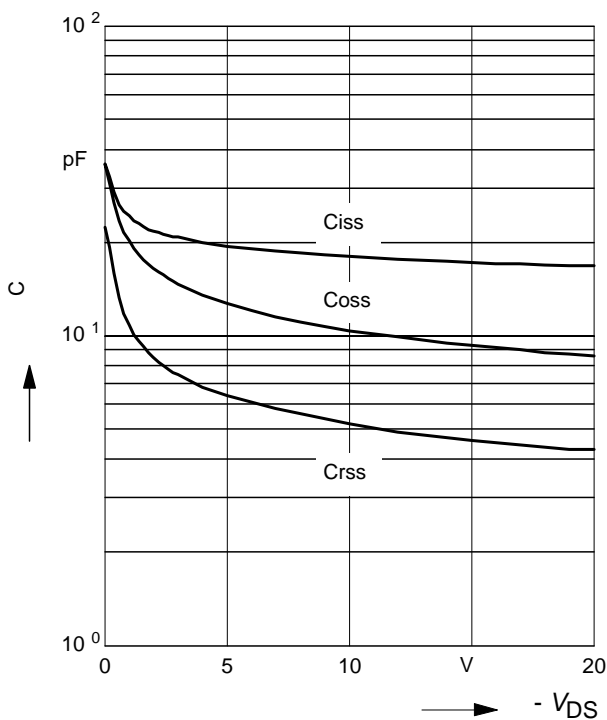
parameter:  $V_{GS} = V_{DS}$



**11 Typ. capacitances**

$$C = f(V_{DS})$$

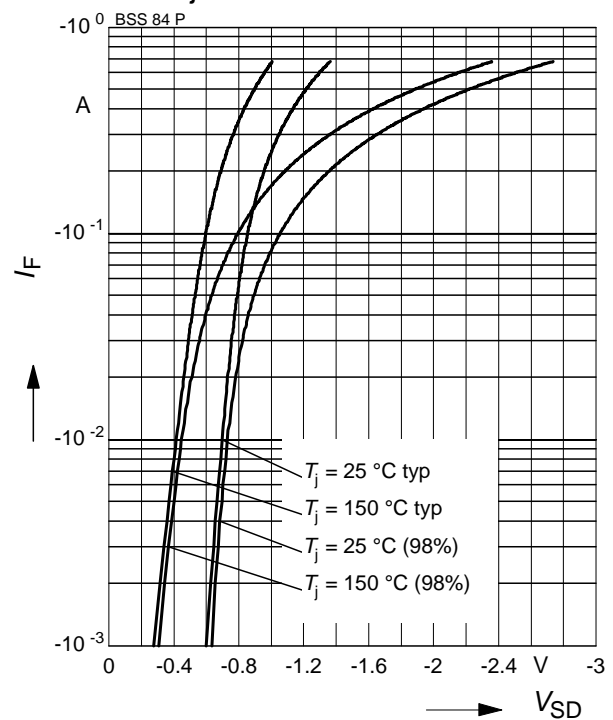
parameter:  $V_{GS}=0$ ,  $f=1 \text{ MHz}$



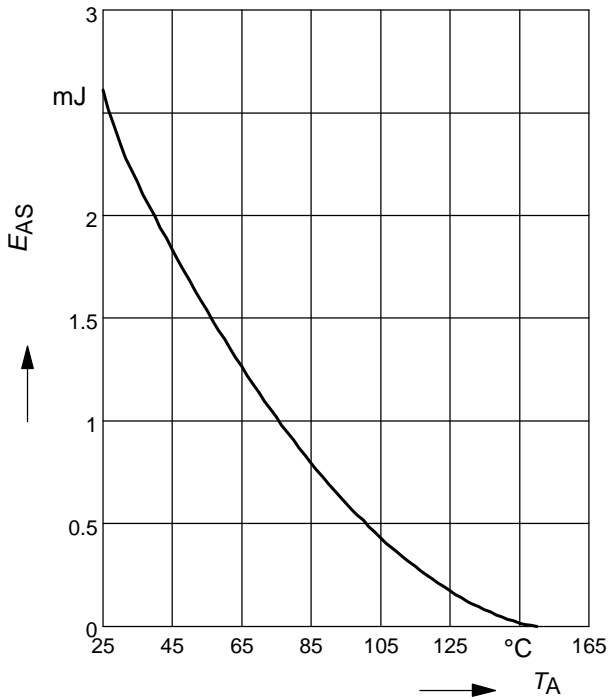
**12 Forward character. of reverse diode**

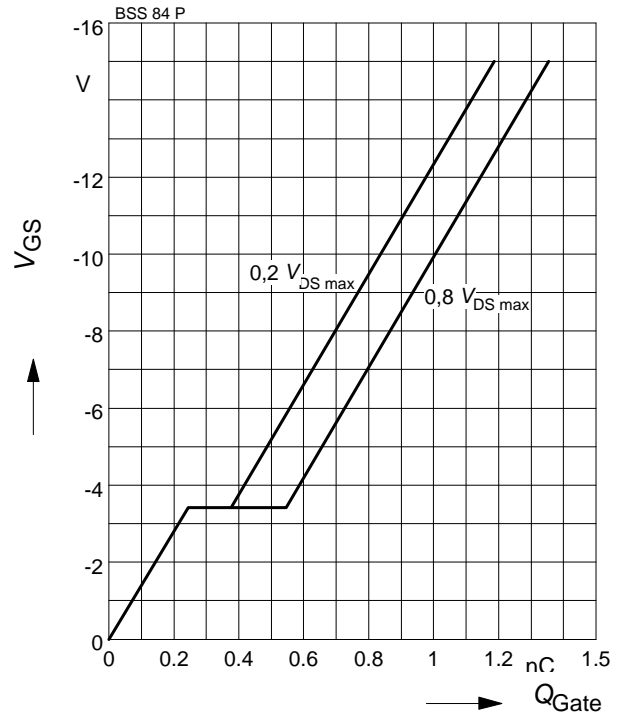
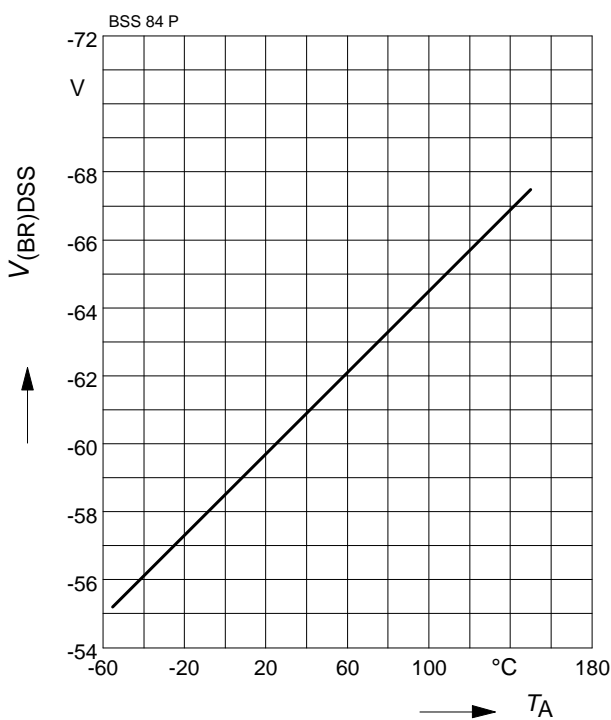
$$I_F = f(V_{SD})$$

parameter:  $T_j$ ,  $t_p = 80 \mu\text{s}$



**13 Typ. avalanche energy**
 $E_{AS} = f(T_A)$ , parameter:

 $I_D = -0.17 \text{ A}$  ,  $V_{DD} = -25 \text{ V}$ ,  $R_{GS} = 25 \Omega$ 

**14 Typ. gate charge**
 $V_{GS} = f(Q_{Gate})$ 

parameter:  $I_D = -0.17 \text{ A}$  pulsed;  $T_j = 25 \text{ °C}$ 

**15 Drain-source breakdown voltage**
 $V_{(BR)DSS} = f(T_A)$ 


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